

# PRODUCT DATA SHEET



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Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



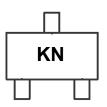
# 2SK3019

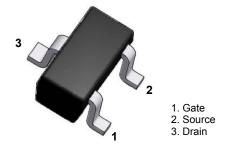
# P-Channel Enhancement Mode Power MOSFET

#### **Specification Features:**

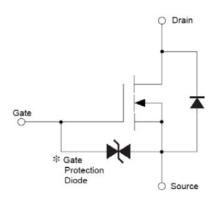
- Low On-resistance
- Fast Switching Speed
- Low Voltage Drive Makes This Device Ideal for Portable Equipment
- Easily Designed Drive Circuits
- Easy to Parallel
- RoHS Compliant & Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

#### **Device Marking Code:**









# **Electrical Symbol**

#### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>DS</sub>	Drain-Source Voltage	30	V	
V <sub>GS</sub>	Continuous Gate-Source Voltage	$\pm$ 20V	V	
ID	Continuous Drain Current	100	mA	
PD	Power Dissipation	150	mW	
R <sub>0JA</sub>	Thermal Resistance from Junction to Ambient	833	°C /W	
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	°C	
TJ	Operating Junction Temperature	+125	°C	

These ratings are limiting values above which the serviceability of the device may be impaired.



## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Тур	Max	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V, I <sub>D</sub> =10uA	30			Volts
I <sub>GSS</sub>	Gate-Body Leakage	$V_{DS}$ =0V, $V_{GS}$ = $\pm$ 20V			±1	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA

#### On Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Тур	Max	Unit
V <sub>th(GS)</sub>	Gate-Threshold Voltage	V <sub>DS</sub> = 3V, I <sub>D</sub> =100uA	0.8		1.5	Volts
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =4V, I <sub>D</sub> =10mA			8	Ω
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1mA			13	Ω
<b>g</b> fs	Forward Trans Conductance	V <sub>DS</sub> =3V, I <sub>D</sub> =10mA	20			ms
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	I <sub>S</sub> =115mA, V <sub>GS</sub> =0V			1.2	V

## **Dynamic Characteristics**

Symbol	Parameter	Test Condition	Limits			11
			Min	Тур	Max	Unit
Ciss	Input Capacitance	V <sub>DS</sub> = 5V		13		pF
Coss	Output Capacitance	$V_{GS} = 0V$		9		pF
Crss	Reverse Transfer Capacitance	f = 1.0MHz		4		pF

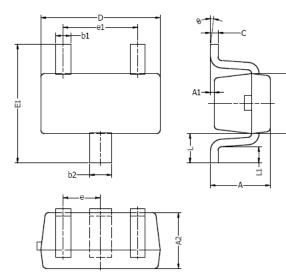
## Switching Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Тур	Max	Unit
t <sub>D(on)</sub>	Turn-on Time	$V_{DD}$ =5V, R <sub>L</sub> =500 $\Omega$ ,		15		nS
t <sub>D(off)</sub>	Turn-off Time	I <sub>D</sub> =10mA, V <sub>Gs</sub> =5V, R <sub>G</sub> = 10Ω		80		nS

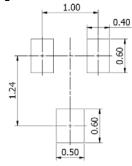




# SOT-523 Package Outline



#### Typical Soldering Pattern:



DIM	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
А	0.70	0.90	0.028	0.035	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.80	0.028	0.031	
b1	0.15	0.25	0.006	0.010	
b2	0.25	0.35	0.010	0.014	
с	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
E	0.70	0.90	0.028	0.035	
E1	1.45	1.75	0.057	0.069	
е	0.50 TYP.		0.020 TYP.		
e1	0.90	1.10	0.035	0.043	
L	0.40 REF.		0.016 REF.		
L1	0.10	0.30	0.004	0.012	
θ	<b>0</b> °	<b>8</b> <sup>0</sup>	<b>0</b> °	<b>8</b> °	

# NOTES:

Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



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